









SN74HC74, SN54HC74

SCLS094F - DECEMBER 1982 - REVISED JUNE 2021

SNx4HC74 Dual D-Type Positive-Edge-Triggered Flip-Flops With Clear and Preset

1 Features

- **Buffered inputs**
- Wide operating voltage range: 2 V to 6 V
- Wide operating temperature range: -40°C to +85°C
- Supports fanout up to 10 LSTTL loads
- Significant power reduction compared to LSTTL logic ICs

2 Applications

- Convert a momentary switch to a toggle switch
- Divide a clock signal by 2 or 4

3 Description

The SNx4HC74 devices contain two independent positive-edge-triggered flip-flops asynchronous preset and clear pins for each.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN74HC74D	SOIC (14)	8.70 mm × 3.90 mm
SN74HC74DB	SSOP (14)	6.50 mm × 5.30 mm
SN74HC74N	PDIP (14)	19.30 mm × 6.40 mm
SN74HC74NS	SO (14)	10.20 mm × 5.30 mm
SN74HC74PW	TSSOP (14)	5.00 mm × 4.40 mm
SN54HC74J	CDIP (14)	21.30 mm × 7.60 mm
SN54HC74W	CFP (14)	9.20 mm × 6.29 mm
SN54HC74FK	LCCC (20)	8.90 mm × 8.90 mm

For all available packages, see the orderable addendum at the end of the data sheet.

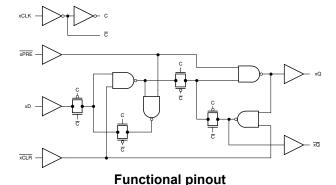




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4 Revision History

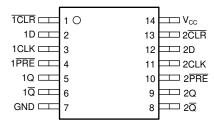
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision E (December 2015) to Revision F (June 2021)

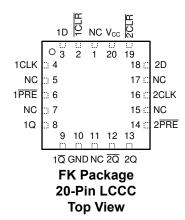
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5 Pin Configuration and Functions



D, DB, N, NS, PW, J, or W Package 14-Pin SOIC, SSOP, PDIP, SO, TSSOP, CDIP, or CFP Top View



Pin Functions

	PIN			
NAME	D, DB, N, NS, PW, J, or W	FK	I/O	DESCRIPTION
1 CLR	1	2	Input	Channel 1, Clear Input, Active Low
1D	2	3	Input	Channel 1, Data Input
1CLK	3	4	Input	Channel 1, Positive edge triggered clock input
1 PRE	4	6	Input	Channel 1, Preset Input, Active Low
1Q	5	8	Output	Channel 1, Output
1 Q	6	9	Output	Channel 1, Inverted Output
GND	7	10	_	Ground
2 Q	8	12	Output	Channel 2, Inverted Output
2Q	9	13	Output	Channel 2, Output
2 PRE	10	14	Input	Channel 2, Preset Input, Active Low
2CLK	11	16	Input	Channel 2, Positive edge triggered clock input
2D	12	18	Input	Channel 2, Data Input
2 CLR	13	19	Input	Channel 2, Clear Input, Active Low
V _{CC}	14	20	_	Positive Supply
NC		1, 5, 7, 11, 15, 17	_	Not internally connected



6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V _{CC}	Supply voltage		-0.5	7	V
I _{IK}	Input clamp current ⁽²⁾	$V_I < -0.5 \text{ V or } V_I > V_{CC}$		±20	mA
I _{OK}	Output clamp current ⁽²⁾	$V_I < -0.5 \text{ V or } V_I > V_{CC}$		±20	mA
Io	Continuous output current	V _O = 0 to V _{CC}		±25	mA
	Continuous current through V _{CC} or GND			±50	mA
TJ	Junction temperature ⁽³⁾			150	°C
T _{stg}	Storage temperature		– 65	150	°C

- (1) Stresses beyond those listed under Absolute Maximum Rating may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Condition. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) Guaranteed by design.

6.2 ESD Ratings

			VALUE	UNIT
V	Clastrostatia dia sharga	Human-body model (HBM), per ANSI/ESDA/ JEDEC JS-001 ⁽¹⁾	±2000	V
V _(ESD)		Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	V

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

			MIN	NOM	MAX	UNIT
V _{CC}	Supply voltage		2	5	6	V
		V _{CC} = 2 V	1.5			
V_{IH}	High-level input voltage	V _{CC} = 4.5 V	3.15			V
		V _{CC} = 6 V	4.2			
		V _{CC} = 2 V			0.5	
V _{IL}	Low-level input voltage	V _{CC} = 4.5 V			1.35	V
		V _{CC} = 6 V			1.8	
VI	Input voltage		0		V _{CC}	V
Vo	Output voltage		0		V _{CC}	V
		V _{CC} = 2 V			1000	
Δt/Δν	Input transition rise and fall rate	V _{CC} = 4.5 V			500	ns
		V _{CC} = 6 V			400	
	Operating free air temperature	SN54HC00	-55		125	°C
T_A	Operating free-air temperature	SN74HC00	-40		85	C

6.4 Thermal Information

				SN74HC74				SN54HC74		
Т	HERMAL METRIC(1)	D (SOIC)	DB (SSOP)	N (PDIP)	NS (SO)	PW (TSSOP)	J (CDIP)	W (CFP)	FK (LCCC)	UNIT
		14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	14 PINS	20 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	133.6	107.7	61.9	122.6	151.7	N/A	N/A	N/A	°C/W
R _θ JC(to p)	Junction-to-case (top) thermal resistance	89.0	57.4	49.7	81.8	79.4	15.05	14.65	5.61	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	89.5	57.9	41.7	83.8	94.7	N/A	N/A	N/A	°C/W
Ψ_{JT}	Junction-to-top characterization parameter	45.5	17.6	29.3	45.4	25.2	N/A	N/A	N/A	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	89.1	57.2	41.4	83.4	94.1	N/A	N/A	N/A	°C/W
R _θ JC(bo	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	N/A	N/A	N/A	N/A	N/A	°C/W

For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application

6.5 Electrical Characteristics - 74

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

					C																			
P	ARAMETER	TEST	CONDITIONS	V _{CC}		25°C		-40°	C to 85°	C	UNIT													
					MIN	TYP	MAX	MIN	TYP	MAX														
				2 V	1.9	1.998		1.9																
		., .,	$I_{OH} = -20 \mu A$	4.5 V	4.4	4.499		4.4																
V _{OH}	High-level output voltage	$V_I = V_{IH}$ or V_{IL}		6 V	5.9	5.999		5.9			V													
	output rollings	0. V _{IL}	I _{OH} = -4 mA	4.5 V	3.98	4.3		3.84																
						I _{OH} = -5.2 mA	6 V	5.48	5.8		5.34													
		V _I = V _{IH} or V _{IL}		2 V		0.002	0.1			0.1														
			I _{OL} = 20 μA	4.5 V		0.001	0.1			0.1														
V _{OL}	Low-level output voltage																6 V		0.001	0.1			0.1	V
	Vollage															or V _{IL}	or V _{IL}	or v _{IL}	JI VIL	I _{OL} = 4 mA	4.5 V		0.17	0.26
			I _{OL} = 5.2 mA	6 V		0.15	0.26			0.33														
I _I	Input leakage current	V _I = V _{CC} c	or O	6 V			±0.1			±1	μA													
I _{CC}	Supply current	V _I = V _{CC} or 0	I _O = 0	6 V			4			40	μA													
Ci	Input capacitance			2 V to 6 V		3	10			10	pF													



6.6 Electrical Characteristics - 54

over operating free-air temperature range; typical values measured at TA = 25°C (unless otherwise noted).

			<u> </u>				Opera	ting free	air tem	peratur	e (T _A)																					
ı	PARAMETER	TEST CO	NDITIONS	V _{cc}		25°C		–40°	C to 85°	,C	-55°C	to 125	°C	UNIT																		
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX																			
				2 V	1.9	1.998		1.9			1.9																					
			I _{OH} = -20 μΑ	4.5 V	4.4	4.499		4.4			4.4																					
Vou	High-level	V _I = V _{IH} or	F., .	6 V	5.9	5.999		5.9			5.9																					
- 011	output voltage	V _{IL}	I _{OH} = -6 mA	4.5 V	3.98	4.3		3.84			3.7			V																		
							I _{OH} = -7.8 mA	6 V	5.48	5.8		5.34			5.2																	
				2 V		0.002	0.1			0.1			0.1																			
			I _{OL} = 20 uA	4.5 V		0.001	0.1			0.1			0.1																			
V _{OL}	Low-level output		F., .	6 V		0.001	0.1			0.1			0.1	$\mid v \mid$																		
OL	voltage		V_{IL}	V _{IL}		V_{IL}	V_{IL}	V_{IL}	V_{IL}		1.,			V _{IL}				_	Ľ	10		I_{OL} = 6 mA	4.5 V		0.17	0.26			0.33			0.4
			I _{OL} = 7.8 mA	6 V		0.15	0.26			0.33			0.4																			
I	Input leakage current	V _I = V _{CC} or		6 V			±0.1			±1			±1	μА																		
I _{CC}	Supply current	V _I = V _{CC} or 0	I _O = 0	6 V			2			20			40	μА																		
Ci	Input capacitance			2 V to 6 V		3	10			10			10	pF																		

6.7 Timing Requirements - 74

over operating free-air temperature range (unless otherwise noted)

				O	perating	free-air	temperati	ure (T _A)		
			V _{cc}		25°C		–40°	C to 85°	С	UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	
			2 V			6			5	
f _{clock}	Clock frequency		4.5 V			31			25	MHz
			6 V	0		36	0		29	
			2 V			100			125	
		PRE or CLR low	4.5 V			20			25	
	Pulse duration		6 V			14			21	20
t _w			2 V			80			100	ns
		CLK high or low	4.5 V			16			20	
			6 V			14			17	
			2 V			100			125	
		Data	4.5 V			20			25	
	Setup time before CLK↑		6 V			17			21	no
t _{su}	Setup time before CLK		2 V			25			30	ns
		PRE or CLR inactive	4.5 V			5			6	
			6 V			4			5	
			2 V	0			0			
th	Hold time, data after CLK↑		4.5 V	0			0			ns
			6 V	0			0			



6.8 Timing Requirements - 54

over operating free-air temperature range; typical values measured at TA = 25°C (unless otherwise noted).

	1 5 1	3 , ,,		Operating free-air temperature (T _A) 25°C									
			V _{CC}		25°C		–40°	C to 8	5°C	-55°	C to 12	5°C	UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
			2 V			6			5			4.2	
f _{clock}	Clock frequency		4.5 V			31			25			21	ns
			6 V	0		36	0		29	0		25	
			2 V			100			125			150	
		PRE or CLR low	4.5 V			20			25			30	
	Pulse duration		6 V			14			21			25	ns
t _w		CLK high or low	2 V			80			100			120	115
			4.5 V			16			20			24	
			6 V			14			17			20	
			2 V			100			125			150	
		Data	4.5 V			20			25			30	
	Setup time before CLK↑		6 V			17			21			25]
t _{su}	Setup time before CLK		2 V			25			30			40	ns
		PRE or CLR inactive	4.5 V			5			6			8	
			6 V			4			5			7	
			2 V	0			0			0			
th	Hold time, data after CLK↑		4.5 V	0			0			0			MHz
			6 V	0			0			0			

6.9 Switching Characteristics - 74

over operating free-air temperature range (unless otherwise noted)

	-				Op	erating	free-air	temperat	ure (T _A)					
	PARAMETER	FROM	то	Vcc		25°C			-40°C to 85°C					
					MIN	TYP	MAX	MIN	TYP	MAX				
				2 V	6	10		6						
f _{max}				4.5 V	31	50		25			MHz			
				6 V	36	60		29						
				2 V		70	230			290				
		PRE or CLR	Q or Q	4.5 V		20	46			58				
.	Propagation delay	52 . t		6 V		15	39			49	ns			
t _{pd}	Fropagation delay			2 V		70	175			220	115			
		CLK	Q or $\overline{\mathbf{Q}}$	4.5 V		20	35			44				
				6 V		15	30			39				
			Q or Q	2 V		28	75			95				
t _t	Transition-time			4.5 V		8	15			19	ns			
		Transition time					6 V		6	13			16	



6.10 Switching Characteristics - 54

over operating free-air temperature range; typical values measured at TA = 25°C (unless otherwise noted).

						(Operati	ng free	-air ten	nperatu	ıre (T _A)			
	PARAMETER		то	V _{cc}		25°C		-40°	°C to 8	5°C	-55°C	C to 12	5°C	UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
				2 V	6	10		6			4.2			
f _{max}				4.5 V	31	50		25			21			MHz
				6 V	36	60		29			25			
		PRE or CLR	Q or Q	2 V		70	230			290			345	
				4.5 V		20	46			58			69	
	Propagation delay			6 V		15	39			49			59	ns
t _{pd}	r Topagation delay		Q or Q	2 V		70	175			220			250	115
		CLK		4.5 V		20	35		,	44			50	
				6 V		15	30			39			42	
			Q or Q	2 V		28	75			95			110	
t _t	Transition-time			4.5 V		8	15			19			22	ns
				6 V		6	13			16			19	

6.11 Operating Characteristics

over operating free-air temperature range; typical values measured at T_A = 25°C (unless otherwise noted).

	PARAMETER	TEST CONDITIONS	V _{CC}	MIN	TYP MAX	UNIT
Cpc	Power dissipation capacitance per gate	No load	2 V to 6 V		35	pF

6.12 Typical Characteristics

 $T_A = 25^{\circ}C$

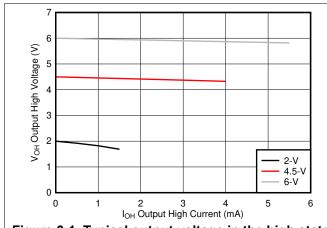


Figure 6-1. Typical output voltage in the high state (V_{OH})

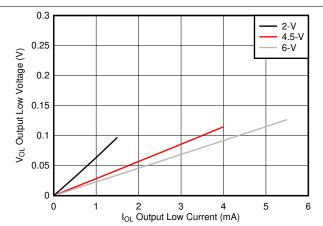
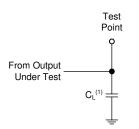


Figure 6-2. Typical output voltage in the low state (V_{OL})

7 Parameter Measurement Information

- Phase relationships between waveforms were chosen arbitrarily. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1 MHz, Z_O = 50 Ω, t_t < 6 ns.
- The outputs are measured one at a time, with one input transition per measurement.



A. C_L= 50 pF and includes probe and jig capacitance.

Figure 7-1. Load Circuit

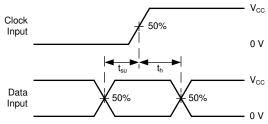
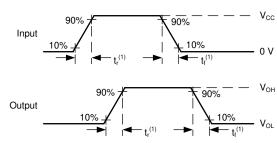


Figure 7-3. Voltage Waveforms Setup and Hold Times



A. t_t is the greater of t_r and t_f .

Figure 7-2. Voltage Waveforms Transition Times

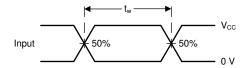
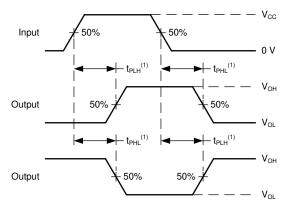


Figure 7-4. Voltage Waveforms Pulse Width



A. The maximum between t_{PLH} and t_{PHL} is used for t_{pd}.

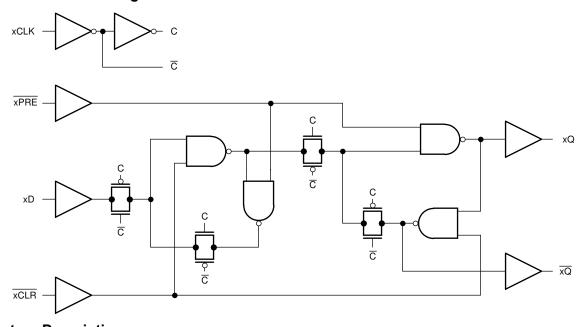
Figure 7-5. Voltage Waveforms Propagation Delays

8 Detailed Description

8.1 Overview

The SNx4HC74 devices contain two independent D-type positive-edge-triggered flip-flops with asynchronous preset and clear pins for each.

8.2 Functional Block Diagram



8.3 Feature Description

8.3.1 Balanced CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The drive capability of this device may create fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to over-current. The electrical and thermal limits defined in the *Section 6.1* must be followed at all times.

The SN74HC74 can drive a load with a total capacitance less than or equal to the maximum load listed in the Section 6.9 connected to a high-impedance CMOS input while still meeting all of the datasheet specifications. Larger capacitive loads can be applied, however it is not recommended to exceed the provided load value. If larger capacitive loads are required, it is recommended to add a series resistor between the output and the capacitor to limit output current to the values given in the Section 6.1.

8.3.2 Standard CMOS Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor from the input to ground in parallel with the input capacitance given in the Section 6.5. The worst case resistance is calculated with the maximum input voltage, given in the Section 6.1, and the maximum input leakage current, given in the Section 6.5, using ohm's law $(R = V \div I)$.

Signals applied to the inputs need to have fast edge rates, as defined by the input transition time in the Section 6.3 to avoid excessive current consumption and oscillations. If a slow or noisy input signal is required, a device with a Schmitt-trigger input should be used to condition the input signal prior to the standard CMOS input.



8.3.3 Clamp Diode Structure

The inputs and outputs to this device have both positive and negative clamping diodes as depicted in Figure 8-1.

CAUTION

Voltages beyond the values specified in the Section 6.1 table can cause damage to the device. The recommended input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

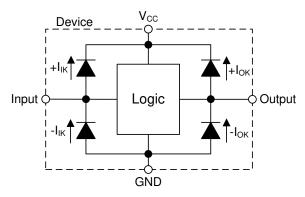


Figure 8-1. Electrical Placement of Clamping Diodes for Each Input and Output

8.4 Device Functional Modes

Table 8-1. Function Table

	INP	OUTPUTS				
PRE	CLR	CLK	D	Q	Q	
L	Н	Х	Х	Н	L	
Н	L	X	X	L	Н	
L	L	X	X	H ⁽¹⁾	H ⁽¹⁾	
Н	Н	1	Н	Н	L	
Н	Н	1	L	L	Н	
Н	Н	L	X	Q_0	\overline{Q}_0	

(1) This configuration is nonstable; that is, it does not persist when PRE or CLR returns to its inactive (high) level.

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

Toggle switches are typically large, mechanically complex and relatively expensive. It is desirable to use a momentary switch instead because they are small, mechanically simple and low cost. Some systems require a toggle switch's functionality but are space or cost constrained and must use a momentary switch instead.

If the data input (D) of the D-type flip-flop is tied to the inverted output (\overline{Q}), then each clock pulse will cause the value at the output (Q) to toggle. The momentary switch can be debounced and connected through a Schmitt-trigger buffer to the clock input (CLK) to toggle the output.

This application also utilizes a power-on reset circuit to ensure that the output always starts in the LOW state when power is applied.

9.2 Typical Application

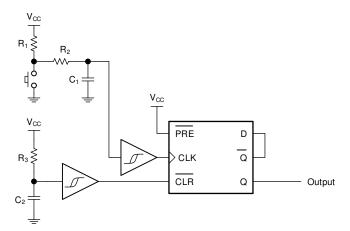


Figure 9-1. Typical application schematic

9.2.1 Design Requirements

9.2.1.1 Power Considerations

Ensure the desired supply voltage is within the range specified in the Section 6.3. The supply voltage sets the device's electrical characteristics as described in the Section 6.5.

The supply must be capable of sourcing current equal to the total current to be sourced by all outputs of the SN74HC74 plus the maximum supply current, I_{CC} , listed in the Section 6.5. The logic device can only source or sink as much current as it is provided at the supply and ground pins, respectively. Be sure not to exceed the maximum total current through GND or V_{CC} listed in the Section 6.1.

Total power consumption can be calculated using the information provided in CMOS Power Consumption and C_{pd} Calculation.

Thermal increase can be calculated using the information provided in Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices.



CAUTION

The maximum junction temperature, $T_J(max)$ listed in the Section 6.1, is an additional limitation to prevent damage to the device. Do not violate any values listed in the Section 6.1. These limits are provided to prevent damage to the device.

9.2.1.2 Input Considerations

Unused inputs must be terminated to either V_{CC} or ground. These can be directly terminated if the input is completely unused, or they can be connected with a pull-up or pull-down resistor if the input is to be used sometimes, but not always. A pull-up resistor is used for a default state of HIGH, and a pull-down resistor is used for a default state of LOW. The resistor size is limited by drive current of the controller, leakage current into the SN74HC74, as specified in the Section 6.5, and the desired input transition rate. A 10-k Ω resistor value is often used due to these factors.

The SN74HC74 has standard CMOS inputs, so input signal edge rates cannot be slow. Slow input edge rates can cause oscillations and damaging shoot-through current. The recommended rates are defined in the Section 6.3.

Refer to the Section 8.3 for additional information regarding the inputs for this device.

9.2.1.3 Output Considerations

The positive supply voltage is used to produce the output HIGH voltage. Drawing current from the output will decrease the output voltage as specified by the V_{OH} specification in the *Section 6.5*. Similarly, the ground voltage is used to produce the output LOW voltage. Sinking current into the output will increase the output voltage as specified by the V_{OL} specification in the *Section 6.5*.

Unused outputs can be left floating. Do not connect outputs directly to V_{CC} or ground.

Refer to Section 8.3 for additional information regarding the outputs for this device.

9.2.1.4 Timing Considerations

The SN74HC74 is a clocked device. As such, it requires special timing considerations to ensure normal operation.

Primary timing factors to consider:

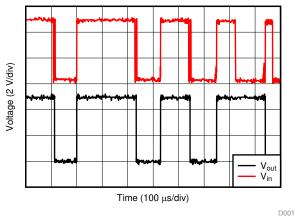
- Maximum clock frequency: the maximum operating clock frequency defined in Section 6.7 is the maximum frequency at which the device is guaranteed to function. This value refers specifically to the triggering waveform, measuring from one trigger level to the next.
- Pulse duration: ensure that the triggering event duration is larger than the minimum pulse duration, as defined in the Section 6.7.
- Setup time: ensure that the data has changed at least one setup time prior to the triggering event, as defined in the Section 6.7.
- Hold time: ensure that the data remains in the desired state at least one hold time after the triggering event, as defined in the Section 6.7.

9.2.2 Detailed Design Procedure

- 1. Add a decoupling capacitor from V_{CC} to GND. The capacitor needs to be placed physically close to the device and electrically close to both the V_{CC} and GND pins. An example layout is shown in the Section 11.
- 2. Ensure the capacitive load at the output is ≤ 70 pF. This is not a hard limit, however it will ensure optimal performance. This can be accomplished by providing short, appropriately sized traces from the SN74HC74 to the receiving device.
- 3. Ensure the resistive load at the output is larger than $(V_{CC} / I_O(max)) \Omega$. This will ensure that the maximum output current from the *Section 6.1* is not violated. Most CMOS inputs have a resistive load measured in megaohms; much larger than the minimum calculated above.

4. Thermal issues are rarely a concern for logic gates, however the power consumption and thermal increase can be calculated using the steps provided in the application report, CMOS Power Consumption and Cpd Calculation

9.2.3 Application Curves



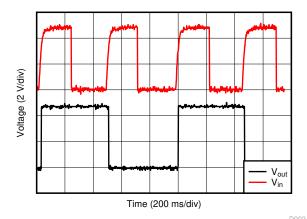


Figure 9-2. Waveform for non-debounced switch.

Figure 9-3. Waveform for debounced switch.



10 Power Supply Recommendations

The power supply can be any voltage between the minimum and maximum supply voltage rating located in the *Section 6.3*. Each V_{CC} terminal should have a bypass capacitor to prevent power disturbance. A 0.1-µF capacitor is recommended for this device. It is acceptable to parallel multiple bypass caps to reject different frequencies of noise. The 0.1-µF and 1-µF capacitors are commonly used in parallel. The bypass capacitor should be installed as close to the power terminal as possible for best results, as shown in *Figure 11-1*.



11 Layout

11.1 Layout Guidelines

When using multiple-input and multiple-channel logic devices inputs must not ever be left floating. In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used. Such unused input pins must not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. All unused inputs of digital logic devices must be connected to a logic high or logic low voltage, as defined by the input voltage specifications, to prevent them from floating. The logic level that must be applied to any particular unused input depends on the function of the device. Generally, the inputs are tied to GND or V_{CC} , whichever makes more sense for the logic function or is more convenient.

11.2 Layout Example

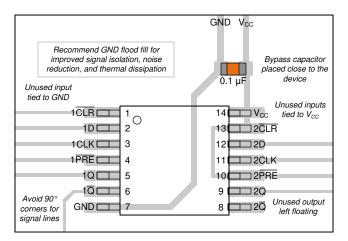


Figure 11-1. Example layout for the SN74HC74



12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation see the following:

- HCMOS Design Considerations
- CMOS Power Consumption and CPD Calculation
- · Designing with Logic

12.2 Support Resources

TI E2E[™] support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

12.3 Trademarks

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All trademarks are the property of their respective owners.

12.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.5 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.





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PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
5962-8405601VCA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8405601VC A SNV54HC74J	Samples
5962-8405601VDA	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	5962-8405601VD A SNV54HC74W	Samples
84056012A	ACTIVE	LCCC	FK	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	84056012A SNJ54HC 74FK	Samples
8405601CA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8405601CA SNJ54HC74J	Samples
8405601DA	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8405601DA SNJ54HC74W	Samples
JM38510/65302B2A	ACTIVE	LCCC	FK	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65302B2A	Samples
JM38510/65302BCA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65302BCA	Samples
JM38510/65302BDA	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65302BDA	Samples
M38510/65302B2A	ACTIVE	LCCC	FK	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65302B2A	Samples
M38510/65302BCA	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65302BCA	Samples
M38510/65302BDA	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	JM38510/ 65302BDA	Samples
SN54HC74J	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	SN54HC74J	Samples
SN74HC74DBR	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC74	Samples
SN74HC74DBRG4	ACTIVE	SSOP	DB	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC74	Samples
SN74HC74DR	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	HC74	Samples
SN74HC74DRG4	ACTIVE	SOIC	D	14	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC74	Samples





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Orderable Device	Status	Package Type	Package Drawing		Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74HC74DT	ACTIVE	SOIC	D	14	250	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC74	Samples
SN74HC74N	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HC74N	Samples
SN74HC74NE4	ACTIVE	PDIP	N	14	25	RoHS & Green	NIPDAU	N / A for Pkg Type	-40 to 85	SN74HC74N	Samples
SN74HC74NSR	ACTIVE	SO	NS	14	2000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	HC74	Samples
SN74HC74PWR	ACTIVE	TSSOP	PW	14	2000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	HC74	Samples
SNJ54HC74FK	ACTIVE	LCCC	FK	20	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	84056012A SNJ54HC 74FK	Samples
SNJ54HC74J	ACTIVE	CDIP	J	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8405601CA SNJ54HC74J	Samples
SNJ54HC74W	ACTIVE	CFP	W	14	1	Non-RoHS & Green	SNPB	N / A for Pkg Type	-55 to 125	8405601DA SNJ54HC74W	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.





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(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF SN54HC74, SN54HC74-SP, SN74HC74:

Catalog: SN74HC74, SN54HC74

Automotive: SN74HC74-Q1, SN74HC74-Q1

● Enhanced Product: SN74HC74-EP, SN74HC74-EP

Military: SN54HC74

• Space: SN54HC74-SP

NOTE: Qualified Version Definitions:

- Catalog TI's standard catalog product
- Automotive Q100 devices qualified for high-reliability automotive applications targeting zero defects
- Enhanced Product Supports Defense, Aerospace and Medical Applications
- Military QML certified for Military and Defense Applications
- Space Radiation tolerant, ceramic packaging and qualified for use in Space-based application



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TAPE AND REEL INFORMATION



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74HC74DBR	SSOP	DB	14	2000	330.0	16.4	8.35	6.6	2.4	12.0	16.0	Q1
SN74HC74DR	SOIC	D	14	2500	330.0	16.8	6.5	9.5	2.1	8.0	16.0	Q1
SN74HC74DR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC74DR	SOIC	D	14	2500	330.0	16.4	6.6	9.3	2.1	8.0	16.0	Q1
SN74HC74DRG4	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC74DT	SOIC	D	14	250	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
SN74HC74NSR	SO	NS	14	2000	330.0	16.4	8.45	10.55	2.5	12.0	16.2	Q1
SN74HC74PWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
SN74HC74PWR	TSSOP	PW	14	2000	330.0	12.4	6.85	5.45	1.6	8.0	12.0	Q1



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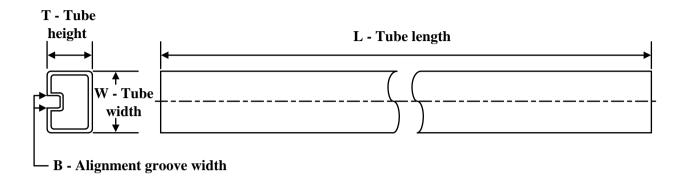
*All dimensions are nominal

All difficulties are florifical							
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74HC74DBR	SSOP	DB	14	2000	356.0	356.0	35.0
SN74HC74DR	SOIC	D	14	2500	364.0	364.0	27.0
SN74HC74DR	SOIC	D	14	2500	340.5	336.1	32.0
SN74HC74DR	SOIC	D	14	2500	366.0	364.0	50.0
SN74HC74DRG4	SOIC	D	14	2500	356.0	356.0	35.0
SN74HC74DT	SOIC	D	14	250	210.0	185.0	35.0
SN74HC74NSR	SO	NS	14	2000	356.0	356.0	35.0
SN74HC74PWR	TSSOP	PW	14	2000	356.0	356.0	35.0
SN74HC74PWR	TSSOP	PW	14	2000	366.0	364.0	50.0



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TUBE

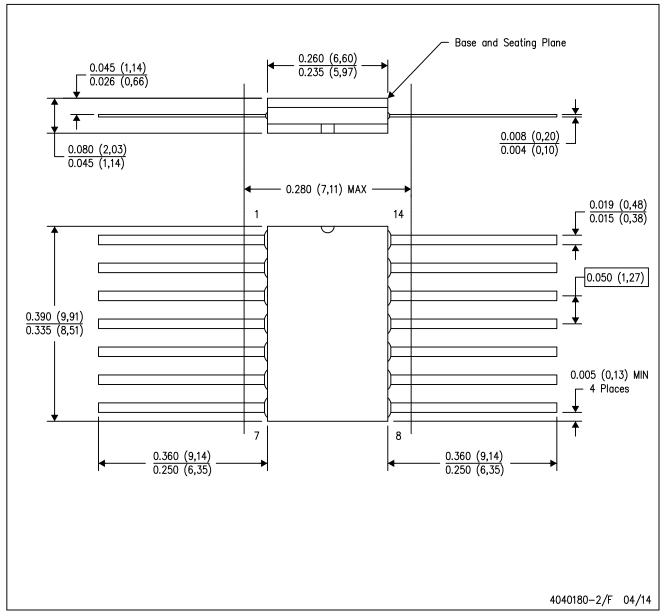


*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
5962-8405601VDA	W	CFP	14	1	506.98	26.16	6220	NA
84056012A	FK	LCCC	20	1	506.98	12.06	2030	NA
8405601DA	W	CFP	14	1	506.98	26.16	6220	NA
JM38510/65302B2A	FK	LCCC	20	1	506.98	12.06	2030	NA
JM38510/65302BDA	W	CFP	14	1	506.98	26.16	6220	NA
M38510/65302B2A	FK	LCCC	20	1	506.98	12.06	2030	NA
M38510/65302BDA	W	CFP	14	1	506.98	26.16	6220	NA
SN74HC74N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC74N	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC74NE4	N	PDIP	14	25	506	13.97	11230	4.32
SN74HC74NE4	N	PDIP	14	25	506	13.97	11230	4.32
SNJ54HC74FK	FK	LCCC	20	1	506.98	12.06	2030	NA
SNJ54HC74W	W	CFP	14	1	506.98	26.16	6220	NA

W (R-GDFP-F14)

CERAMIC DUAL FLATPACK



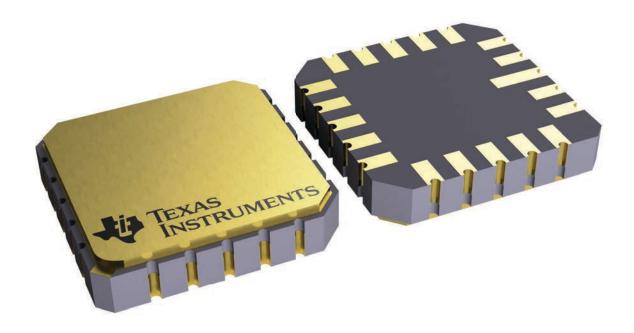
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. This package can be hermetically sealed with a ceramic lid using glass frit.
- D. Index point is provided on cap for terminal identification only.
- E. Falls within MIL STD 1835 GDFP1-F14



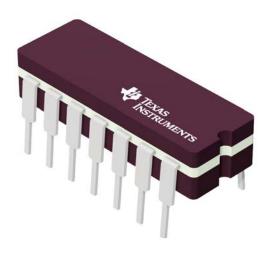
8.89 x 8.89, 1.27 mm pitch

LEADLESS CERAMIC CHIP CARRIER

This image is a representation of the package family, actual package may vary. Refer to the product data sheet for package details.



CERAMIC DUAL IN LINE PACKAGE



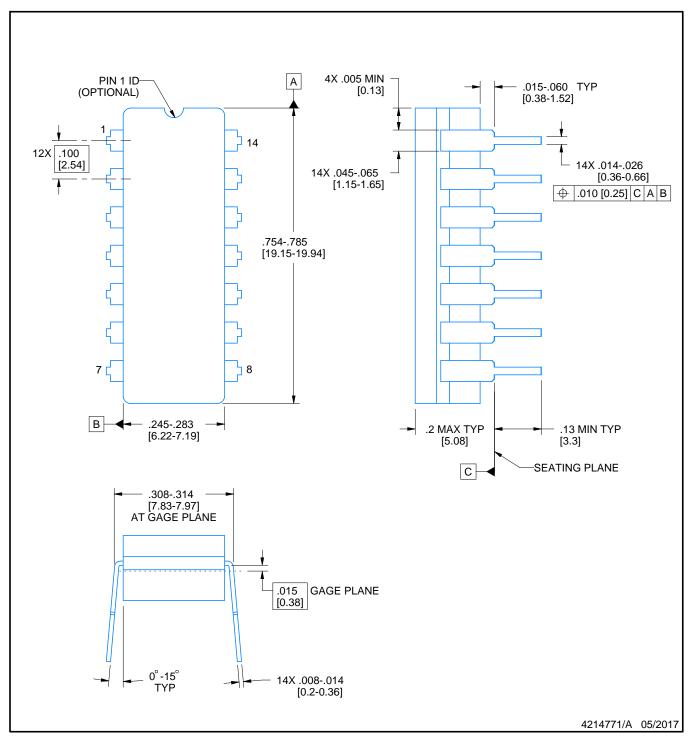
Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

4040083-5/G





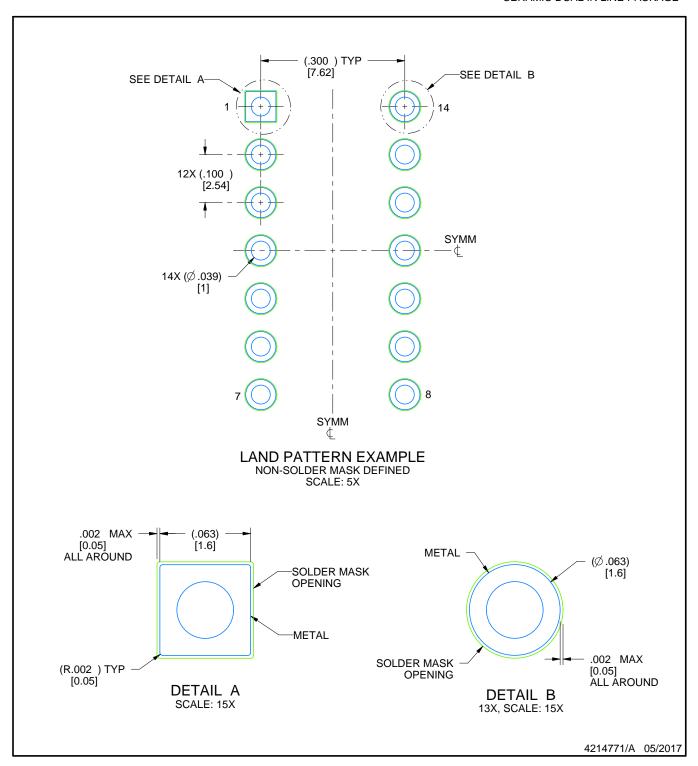
CERAMIC DUAL IN LINE PACKAGE



- 1. All controlling linear dimensions are in inches. Dimensions in brackets are in millimeters. Any dimension in brackets or parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This package is hermitically sealed with a ceramic lid using glass frit.
- His package is remitted by sealed with a ceramic its using glass mit.
 Index point is provided on cap for terminal identification only and on press ceramic glass frit seal only.
 Falls within MIL-STD-1835 and GDIP1-T14.



CERAMIC DUAL IN LINE PACKAGE



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AB.



D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

PLASTIC SMALL OUTLINE



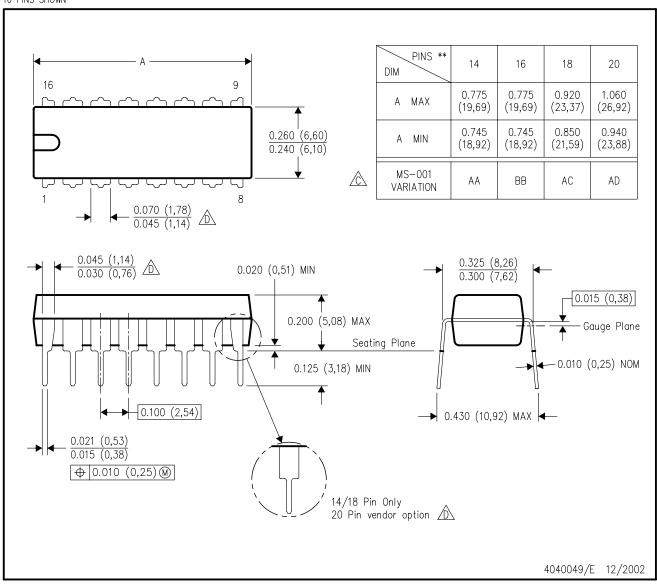
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO-153



N (R-PDIP-T**)

PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



DB (R-PDSO-G**)

PLASTIC SMALL-OUTLINE

28 PINS SHOWN



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion not to exceed 0,15.

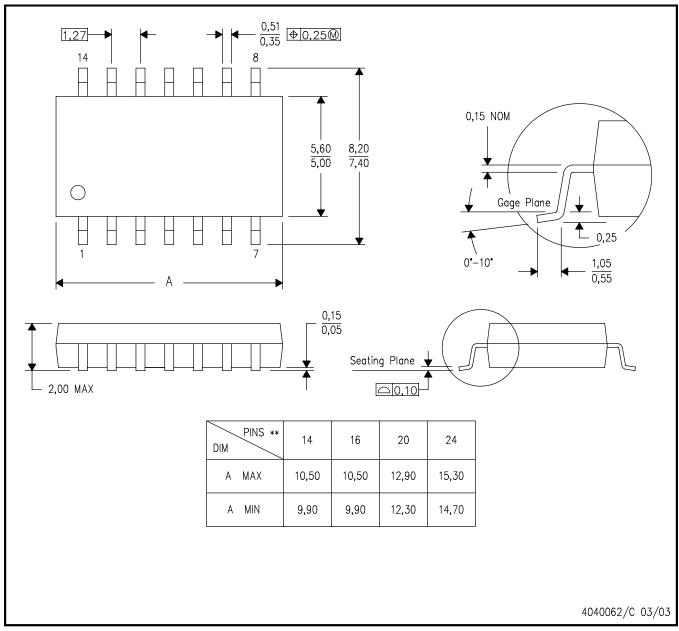
D. Falls within JEDEC MO-150

MECHANICAL DATA

NS (R-PDSO-G**)

14-PINS SHOWN

PLASTIC SMALL-OUTLINE PACKAGE



- All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion, not to exceed 0,15.



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